

STTH806DTI

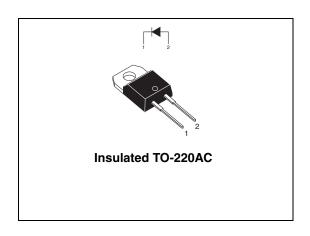
Tandem 600 V hyperfast boost diode

Table 1. Main product characteristics

I _{F(AV)}	8 A
V _{RRM}	600 V
T _{j (max)}	150° C
V _{F (max)}	2.24 V
I _{RM (typ.)}	4 A
t _{rr (typ.)}	13 ns

Features and benefits

- Especially suited as boost diode in continuous mode power factor correctors and hard switching conditions
- Designed for high di/dt operation. Hyperfast recovery current to compete with SiC devices. Allows downsizing of mosfet and heatsinks
- Internal ceramic insulated devices with equal thermal conditions for both 300 V diodes
- Insulation (2500 V_{RMS}) allows placement on same heatsink as mosfet and flexible heatsinking on common or separate heatsink
- Static and dynamic equilibrium of internal diodes are warranted by design
- Package Capacitance: C = 7 pF



Description

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300 V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high dI_E/dt.

Table 2. Order codes

Part number	Marking
STTH806DTI	STTH806DTI

Table 3. Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	600	V
I _{F(RMS)}	RMS forward voltage	14	Α
I _{FSM}	Surge non repetitive forward current	180	Α
T _{stg}	Storage temperature range	-65 to + 150	° C
Tj	Maximum operating junction temperature	150	° C

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Table 4. Thermal parameter

Symbo	Parameter	Value	Unit
R _{th(j-c}	Junction to case thermal resistance	2.6	°C/W

Table 5. Static electrical characteristics

Symbol	Parameter	Test co	nditions	Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25° C	V- - V			10	μA
'R`	IR V Reverse leakage current	T _j = 125° C	$V_R = V_{RRM}$		15	100	μΑ
V _F ⁽²⁾	Forward voltage drop	T _j = 25° C	I _E = 8 A			3.6	V
V _F ⁽²⁾ Forward voltage drop	T _j = 150° C			1.95	2.4	V	

- 1. Pulse test: tp = 100 ms, δ < 2%
- 2. Pulse test: tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 1.7 \text{ x } I_{F(AV)} + 0.087 I_{F}^{2}_{(RMS)}$$

Table 6. Dynamic characteristics

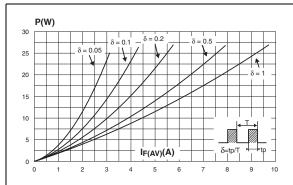
Symbol	Parameter	Test conditions			Тур	Max	Unit
			$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}, I_R = 1 \text{ A}$		13		
t _{rr}	Reverse recovery time	T _j = 25° C	$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$			30	ns
I _{RM}	Reverse recovery current		$T_j = 125^{\circ} \text{ C}$ $I_F = 8 \text{ A}, V_R = 400, VdI_F/dt = -200 \text{ A/µs}$		4	5.5	
S	Reverse recovery softness factor	T _j = 125° C			0.4		Α
Q _{rr}	Reverse recovery charges		ναιριαι – 200 Αγμο		50		

Table 7. Turn-on switching characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
t _{fr}	Forward recovery time	T _j = 25° C	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_F \text{ max}$			200	ns
V _{FP}	Forward recovery voltage	T _j = 25° C	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$			7	V

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Figure 1. Conduction losses versus average Figure 2. Forward voltage drop versus current forward current



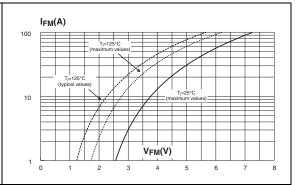
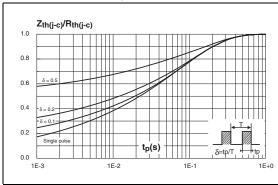


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)



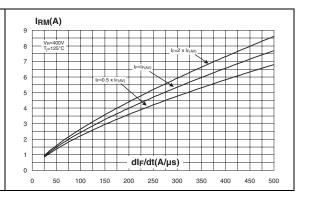
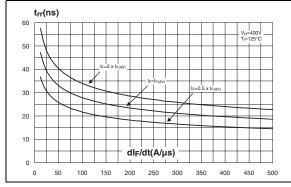
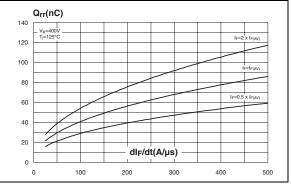


Figure 5. Reverse recovery time versus dl_F/dt Figure 6. (typical values)

Reverse charges versus dl_F/dt (typical values)



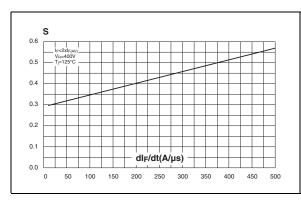


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Figure 7. Softness factor versus dI_F/dt (typical values)

Figure 8. Relative variation of dynamic parameters versus junction temperature (reference: $T_i = 125^{\circ}$ C)



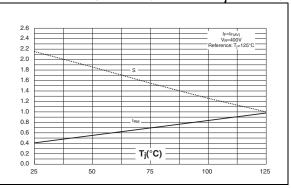
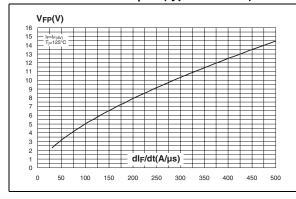
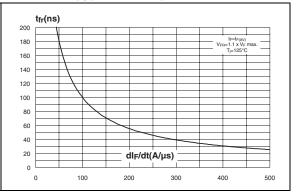


Figure 9. Transient peak forward voltage versus dl_E/dt (typical values)

Figure 10. Forward recovery time versus dl_F/dt (typical values)

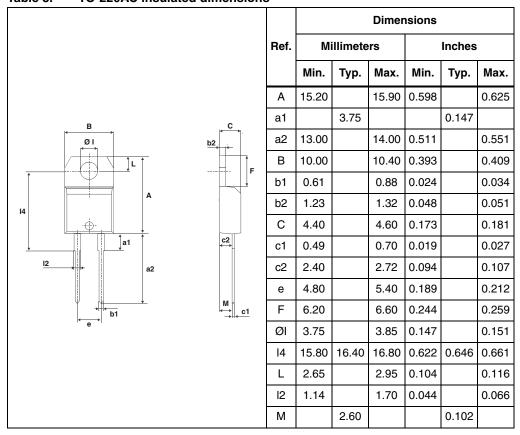




2 Package information

- Epoxy meets UL94, V0
- Cooling method: C
- Recommended torque value: 0.4 to 0.6 Nm

Table 8. TO-220AC insulated dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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3 Ordering information

Table 9. Ordering information

Part number	Marking	Package	Weight	Base qty	Delivery mode
STTH806DTI	STTH806DTI	TO-220AC	2.3 g	50	Tube

4 Revision history

Table 10. Revision history

Date	Revision	Changes
Oct-2003 2A		Initial release
May-2004	May-2004 3 Reformatted	
29-Jun-2005 4		Corrections to typographical errors. No technical changes.
		Reformatted to current standards. Removed I _{PEAK} parameter from <i>Table 3: Absolute ratings (limiting values)</i> .

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